SNx4LVC08A クワッド、2 入力、正論理 AND ゲート

1 特長

- JESD 17 準拠
  250mA 超のラッチアップ性能
- JESD 22 を上回る ESD 保護
  - 2000V、人体モデル (A114-A)
  - 1000V、デバイス帯電モデル (C101)
  - MIL-PRF-38535 準拠の製品については、特に記述のない限り、すべてのパラメータはテスト済みです。その他のすべての製品については、量産プロセスにすべてのパラメータのテストが含まれているとは限りません。
- SN74LVC08A は、1.65V～3.6V の電源電圧で動作します
- SN54LVC08A は、2.0V～3.6V の電源電圧で動作します
- SNx4LVC08A は -40℃～+85℃と -40℃～+125℃で動作を規定
- SN54LVC08A は -55℃～+125℃で動作を規定
- 5.5V までの入力電圧に対応
- 最大 t_{pd} 4.1ns (3.3V 時)
- V_{OLP} 標準値 (出力グランド バウンス)
  <0.8V (V_{CC} = 3.3V、T_A = 25℃)
- V_{OHV} 標準値 (出力 V_{OH} アンダーシュート)
  >2V (V_{CC} = 3.3V、T_A = 25℃)

2 アプリケーション

- サーバー
- LED ディスプレイ
- ネットワーク スイッチ
- I/O エクスパンダ
- ベース ステーション プロセッサ ボード

3 概要

SN54LVC08A クワッド 2 入力正論理 AND ゲートは 2.7V～3.6V の V_{CC} で動作するように設計されており、SN74LVC08A クワッド 2 入力正論理 AND ゲートは 1.65V～3.6V の V_{CC} で動作するように設計されています。

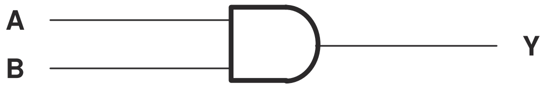
SNx4LVC08A デバイスはブール関数 $Y = A \bullet B$ or $Y = \overline{\overline{A} + \overline{B}}$ を正論理で実行します。

入力は 3.3V または 5V のデバイスから駆動できます。この機能により、3.3V と 5V が混在するシステム環境での変換装置としてこのデバイスを使用できます。

製品情報

部品番号	パッケージ (1)	パッケージ サイズ (2)	本体サイズ (3)
SNx4LVC08A	BQA (WQFN、14)	3mm × 2.5mm	3mm × 2.5mm
	D (SOIC、14)	8.65mm × 6mm	8.65mm × 3.91mm
	DB (SSOP、14)	6.2mm × 7.8mm	6.20mm × 5.30mm
	NS (SOP、14)	10.2mm × 7.8mm	10.30mm × 5.30mm
	PW (TSSOP、14)	5mm × 4.4mm	5.00mm × 4.40mm
	RGY (VQFN、14)	3.5mm × 3.5mm	3.50mm × 3.50mm
	FK (LCCC、20)	8.9mm × 8.9mm	8.89mm × 8.89mm
	J (CDIP、14)	19.55mm × 7.9mm	19.55mm × 6.7mm
	W (CFP、14)	9.21mm × 9mm	9.21mm × 6.28mm

(1) 詳細については、セクション 11 を参照してください。
(2) パッケージ サイズ (長さ × 幅) は公称値であり、該当する場合はピンも含まれます。
(3) 本体サイズ (長さ×幅) は公称値であり、ピンは含まれません。



各ゲートの論理図
(正論理)

English Data Sheet: SCAS283

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4 Pin Configuration and Functions

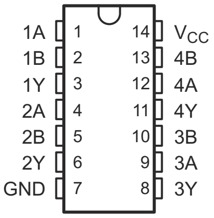


図 4-1. D, DB, NS, J, W, or PW Package 14-Pin SOIC, SSOP, SOP, CDIP, or TSSOP (Top View)

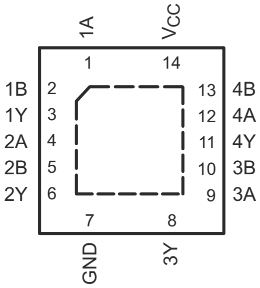


図 4-2. BQA or RGY Package 14-Pin WQFN or VQFN (Top View)

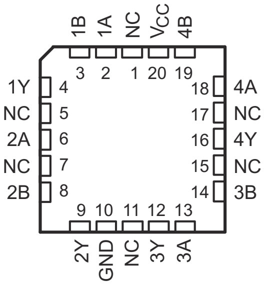


図 4-3. FK Package 20-Pin LCCC (Top View)

表 4-1. Pin Functions

PIN			TYPE	DESCRIPTION
NAME	**SOIC, SSOP, SOP, CDIP, TSSOP, VQFN,WQFN**	**LCCC**		
1A	1	2	I	Channel 1 input A
1B	2	3	I	Channel 1 input B
1Y	3	4	O	Channel 1 output
2A	4	6	I	Channel 2 input A
2B	5	8	I	Channel 2 input B
2Y	6	9	O	Channel 2 output
GND	7	10	Ground	Ground
3Y	8	12	O	Channel 3 output
3A	9	13	I	Channel 3 input A
3B	10	14	I	Channel 3 input B
4Y	11	16	O	Channel 4 output
4A	12	18	I	Channel 4 input A
4B	13	19	I	Channel 4 input B
V_{CC}	14	20	Power	Positive supply
Thermal Information(1)			—	The thermal pad can be connected to GND or left floating. Do not connect to any other signal or supply.
NC(2)	—	1	—	No connect
		5		
		7		
		11		
		15		
		17		

(1) For BQA package only.
(2) NC – No internal connection

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	6.5	V
V_I	Input voltage(2)		–0.5	6.5	V
V_O	Output voltage(2) (3)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	$V_I < 0$		–50	mA
I_{OK}	Output clamp current	$V_O < 0$		–50	mA
I_O	Continuous output current			±50	mA
	Continuous current through V_{CC} or GND			±100	mA
P_{tot}	Power dissipation(4) (5)	T_A = –40°C to +125°C		500	mW
T_J	Junction temperature		–65	150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
(3) The value of V_{CC} is provided in the *Recommended Operating Conditions* table.
(4) For the D package: above 70°C, the value of P_{tot} derates linearly with 8 mW/K.
(5) For the DB, NS, and PW packages: above 60°C, the value of P_{tot} derates linearly with 5.5 mW/K.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	
		Machine Model (MM) A115-A	200	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions, SN54LVC08A

over operating free-air temperature range (unless otherwise noted)(1)

			SN54LVC08A		UNIT
			–55°C to +125°C		
			MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7V to 3.6V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7V to 3.6V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7V		–12	mA
		V_{CC} = 3V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7V		12	mA
		V_{CC} = 3V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate			8	ns/V

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See *Implications of Slow or Floating CMOS Inputs*, SCBA004.

5.4 Recommended Operating Conditions, SN74LVC08A

over operating free-air temperature range (unless otherwise noted)(1)

			SN74LVC08A						UNIT
			T_A = 25°C		–40°C to +85°C		–40°C to +125°C		
			MIN	MAX	MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	1.65	3.6	1.65	3.6	1.65	3.6	V
		Data retention only	1.5		1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 1.65V to 1.95V	0.65 × V_{CC}		0.65 × V_{CC}		0.65 × V_{CC}		V
		V_{CC} = 2.3V to 2.7V	1.7		1.7		1.7		
		V_{CC} = 2.7V to 3.6V	2		2		2		
V_{IL}	Low-level input voltage	V_{CC} = 1.65V to 1.95V		0.35 × V_{CC}		0.35 × V_{CC}		0.35 × V_{CC}	V
		V_{CC} = 2.3V to 2.7V		0.7		0.7		0.7	
		V_{CC} = 2.7V to 3.6V		0.8		0.8		0.8	
V_I	Input voltage		0	5.5	0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 1.65V		–4		–4		–4	mA
		V_{CC} = 2.3V		–8		–8		–8	
		V_{CC} = 2.7 V		–12		–12		–12	
		V_{CC} = 3V		–24		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 1.65V		4		4		4	mA
		V_{CC} = 2.3V		8		8		8	
		V_{CC} = 2.7V		12		12		12	
		V_{CC} = 3V		24		24		24	
Δt/Δv	Input transition rise or fall rate			8		8		8	ns/V

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See *Implications of Slow or Floating CMOS Inputs*, SCBA004.

5.5 Thermal Information

THERMAL METRIC(1)		SN74LVC08A						UNIT
		BQA (WQFN)	D (SOIC)	DB (SSOP)	NS (SO)	PW (TSSOP)	RGY (LCCC)	
		14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	102.3	127.8	140.4	123.8	150.8	92.1	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	96.8	81.9	65.3	52.7	56.0	56.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	70.9	84.4	60.2	53.9	69.5	27.5	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	16.6	39.6	25.3	17.9	8.9	4.5	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	70.9	83.9	59.6	53.6	68.9	27.7	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	50.1	N/A	N/A	N/A	N/A	19.1	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

5.6 Electrical Characteristics, SN54LVC08A

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LVC08A			UNIT
			–55°C to +125°C			
			MIN	TYP(1)	MAX	
V_{OH}	I_{OH} = –100 µA	2.7V to 3.6V	V_{CC} – 0.2			V
	I_{OH} = –12 mA	2.7V	2.2			
		3V	2.4			
	I_{OH} = –24 mA	3V	2.2			
V_{OL}	I_{OL} = 100 µA	2.7V to 3.6V			0.2	V
	I_{OL} = 12 mA	2.7V			0.4	
	I_{OL} = 24 mA	3V			0.55	
I_I	V_I = 5.5 V or GND	3.6V			±5	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7V to 3.6V			500	µA
C_i	V_I = V_{CC} or GND	3.3V		5		pF

(1) T_A = 25°C

5.7 Electrical Characteristics, SN74LVC08A

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN74LVC08A							UNIT
			T_A = 25°C			–40°C to +85°C		–40°C to +125°C		
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V_{OH}	I_{OH} = –100 µA	1.65V to 3.6V	V_{CC} – 0.2			V_{CC} – 0.2		V_{CC} – 0.3		V
	I_{OH} = –4 mA	1.65V	1.29			1.2		1.05		
	I_{OH} = –8 mA	2.3V	1.9			1.7		1.55		
	I_{OH} = –12 mA	2.7V	2.2			2.2		2.05		
		3V	2.4			2.4		2.25		
	I_{OH} = –24 mA	3V	2.3			2.2		2		
V_{OL}	I_{OL} = 100 µA	1.65V to 3.6V			0.1		0.2		0.3	V
	I_{OL} = 4 mA	1.65V			0.24		0.45		0.6	
	I_{OL} = 8 mA	2.3V			0.3		0.7		0.75	
	I_{OL} = 12 mA	2.7V			0.4		0.4		0.6	
	I_{OL} = 24 mA	3V			0.55		0.55		0.8	
I_I	V_I = 5.5 V or GND	3.6V			±1		±5		±20	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6V			1		10		40	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7V to 3.6V			500		500		5000	µA
C_i	V_I = V_{CC} or GND	3.3V		5						pF

5.8 Switching Characteristics, SN54LVC08A

over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	SN54LVC08A –55°C to +125°C MIN	SN54LVC08A –55°C to +125°C MAX	UNIT
t_{pd}	A or B	Y	2.7V		4.8	ns
			3.3V ± 0.3V	1	4.1	

5.9 Switching Characteristics, SN74LVC08A

over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	SN74LVC08A							UNIT
				T_A = 25°C			–40°C to +85°C		–40°C to +125°C		
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1.8V ± 0.15V	1	5	9.3	1	9.8	1	11.3	ns
			2.5V ± 0.2V	1	2.9	6.4	1	6.9	1	9	
			2.7V	1	3	4.6	1	4.8	1	6	
			3.3V ± 0.3V	1	2.6	3.9	1	4.1	1	5.5	
$t_{sk(o)}$			3.3V ± 0.3V					1		1.5	ns

5.10 Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	f = 10 MHz	1.8 V	7	pF
			2.5 V	9.8	
			3.3 V	10	

5.11 Typical Characteristics

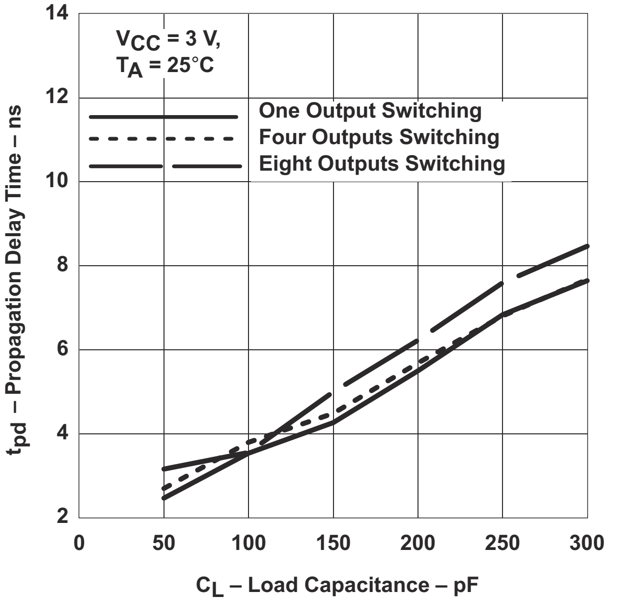


図 5-1. Propagation Delay (Low to High Transition) vs Load Capacitance

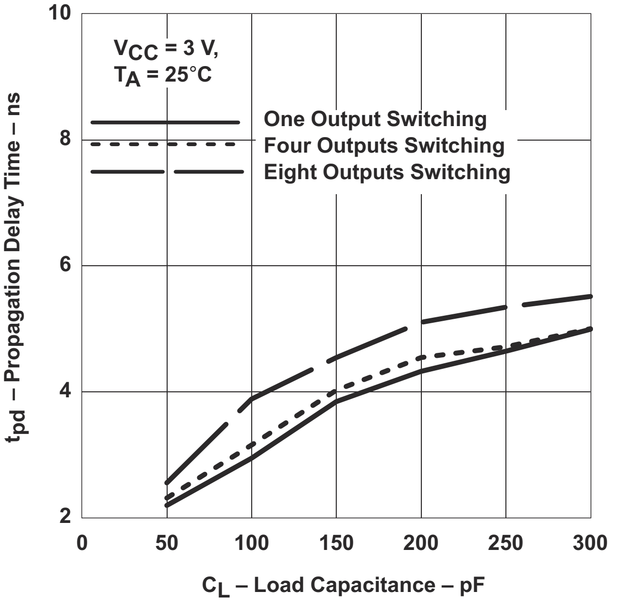
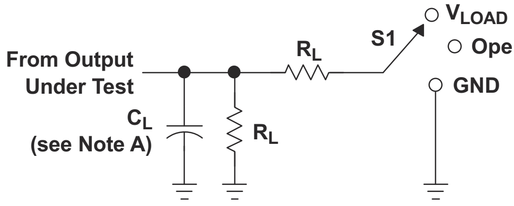


図 5-2. Propagation Delay (High to Low Transition) vs Load Capacitance

6 Parameter Measurement Information

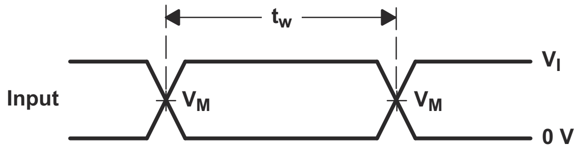
Load Circuit and Voltage Waveforms



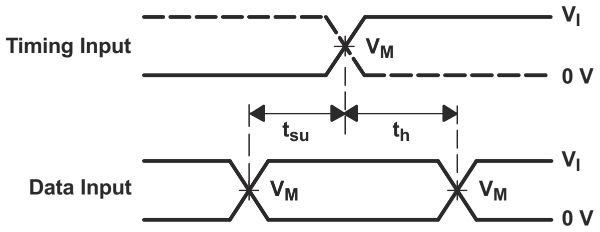
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

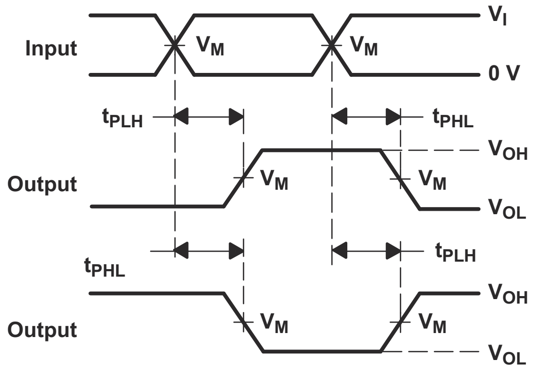
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_D
	V_I	t_r/t_f					
1.8 V ± 0.15 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	1 kΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	500 Ω	0.15 V
2.7 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
3.3 V ± 0.3 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V



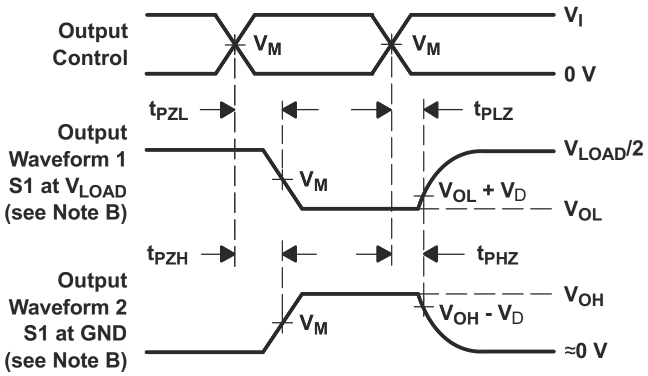
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES:
A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR≤ 10 MHz, Z_O = 50 W.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

7 Detailed Description

7.1 Overview

The SN74LVC08 device contains four 2-input positive AND gate device and performs the Boolean function Y = A × B. This device is useful when multiple AND function is used in the system.

7.2 Functional Block Diagram

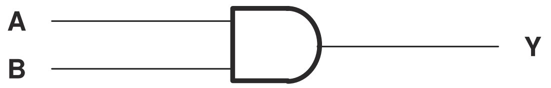


図 7-1. Logic Diagram, Each Gate (Positive Logic)

7.3 Feature Description

7.3.1 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the power output of the device to be limited to avoid thermal runaway and damage due to over-current. The electrical and thermal limits defined the in the *セクション 5.1* must be followed at all times.

7.3.2 Standard CMOS Inputs

Standard CMOS inputs are high impedance and are typically modelled as a resistor in parallel with the input capacitance given in the *セクション 5.6* and *セクション 5.7*. The worst case resistance is calculated with the maximum input voltage, given in the *セクション 5.1*, and the maximum input leakage current, given in the *セクション 5.6* and *セクション 5.7*, using ohm's law (R = V ÷ I).

Signals applied to the inputs need to have fast edge rates, as defined by Δt/Δv in *セクション 5.3* and *セクション 5.4* to avoid excessive currents and oscillations. If a slow or noisy input signal is required, a device with a Schmitt-trigger input should be utilized to condition the input signal prior to the standard CMOS input.

7.3.3 Clamp Diodes

The inputs to this device have negative clamping diodes. The outputs to this device have both positive and negative clamping diodes as shown in 図 7-2.

注意

Voltages beyond the values specified in the *セクション 5.1* table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

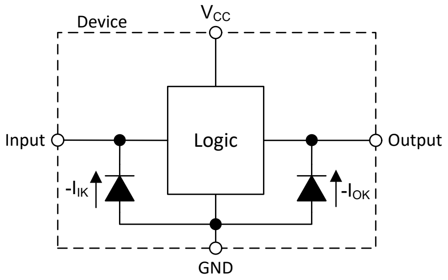


図 7-2. Electrical Placement of Clamping Diodes for Each Input and Output

7.3.4 Over-voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage so long as they remain below the maximum input voltage value specified in the *セクション 5.1*.

7.4 Device Functional Modes

表 7-1 lists the functional modes for the SN54LVC08A and SN74LVC08A devices.

表 7-1. Truth Table

INPUTS		OUTPUT
A	**B**	**Y**
L	L	L
L	H	L
H	L	L
H	H	H

8 Application and Implementation

注

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

8.1 Application Information

The SN74LVC08A is used to drive CMOS device and used for implementing AND logic. The LVC family can support current drive of about 24 mA at 3-V V_{CC}. The inputs for SN74LVC08A are 5.5-V tolerant allowing it to translate down to V_{CC}.

8.2 Typical Application

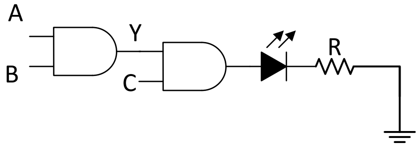


図 8-1. Three Input AND Gate Implementation and Driving LED

8.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

8.2.2 Detailed Design Procedure

SN74LVC08A contains four AND gates in one package which can be used for individual AND function or to implement complex Boolean logic. 図 8-1 shows an example of implementing 3input AND function. AB are inputs for AND gate which are connected to another AND gate. Z= A × B × C. SN74LVC08A support high drive current of 24 mA which can be used to drive LEDs of even Drive low current signal FETs, an example is shown in 図 8-1 TI recommends to use a series resistance to limit the current. If V_{CC} is 3 V, and LED current should be 10 mA, and the forward-voltage of LED is 2.5 V, then R as shown in 図 8-1 is calculated using 式 1:

$$R = (V_{CC} – V_{LED}) / I \qquad (1)$$

$$R = (3 – 2.5) / 0.01 = 50\ \Omega$$

8.2.3 Application Curves

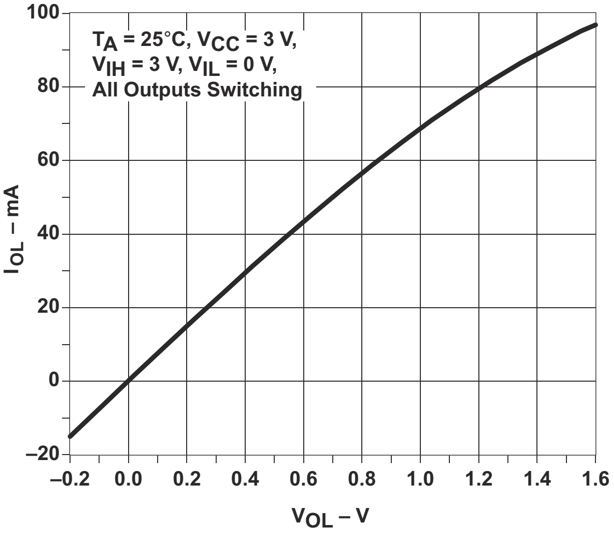


図 8-2. Output Drive Current (I_{OL}) vs LOW-level Output Voltage (V_{OL})

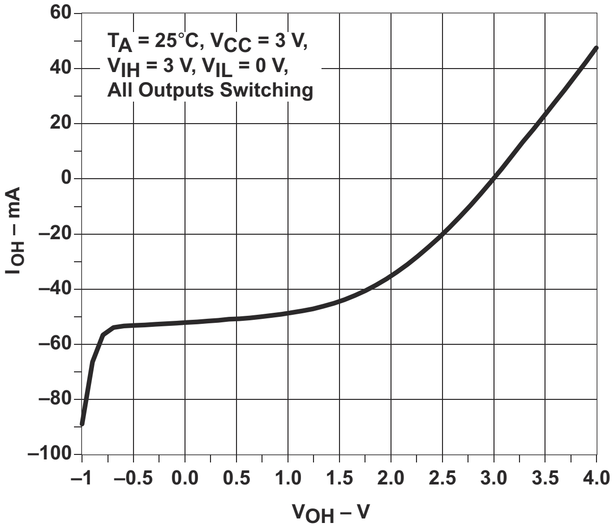


図 8-3. Output Drive Current (I_{OH}) vs HIGH-level Output Voltage (V_{OH})

Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions* table.

The V_{CC} pin must have a good bypass capacitor to prevent power disturbance. TI recommends to use a 0.1-μF capacitor. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1-μF and 1-μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

8.3 Layout

8.3.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in 図 8-4 are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or VCC, whichever makes more sense or is more convenient.

Even low data rate digital signals can have high frequency signal components due to fast edge rates. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. 図 8-5 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

8.3.2 Layout Examples

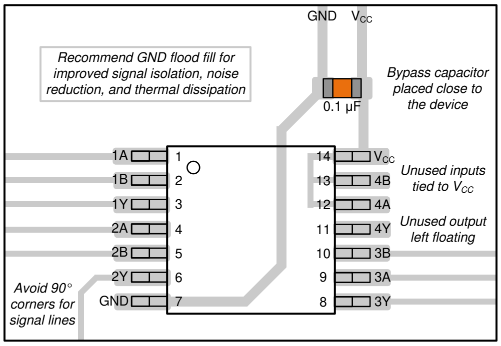


図 8-4. Example Layout

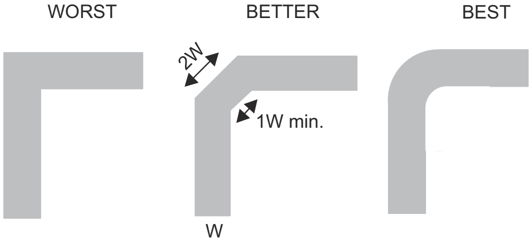


図 8-5. Trace Example

9 Device and Documentation Support

9.1 Documentation Support (Analog)

9.1.1 Related Documentation

For related documentation see the following:

Implications of Slow or Floating CMOS Inputs, SCBA004

9.1.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to order now.

表 9-1. Related Links

PARTS	PRODUCT FOLDER	ORDER NOW	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
SN54LVC08A	Click here	Click here	Click here	Click here	Click here
SN74LVC08A	Click here	Click here	Click here	Click here	Click here

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 サポート・リソース

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9.3.1 Community Resources

9.4 Trademarks

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9.5 静電気放電に関する注意事項

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ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

9.6 用語集

テキサス・インスツルメンツ用語集	この用語集には、用語や略語の一覧および定義が記載されています。

10

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision V (May 2024) to Revision W (July 2024) **Page**

- Updated thermal values for D package from RθJA = 98.6 to 127.8, RθJC(top) = 56.0 to 81.9, RθJB = 53.3 to 84.4, ΨJT = 16.4 to 39.6, ΨJB = 53.0 to 83.9, RθJC(bot) = N/A, all values in °C/W 6

Changes from Revision U (March 2024) to Revision V (May 2024) **Page**

- Updated RθJA values: DB = 112.8 to 140.4, PW = 127.7 to 150.8, RGY = 51.1 to 92.1, NS = 95.1 to 123.8; updated DB, PW, RGY, and NS packages for RθJC(top), RθJB, ΨJT, ΨJB, and RθJC(bot), all values in °C/W.. 6

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
5962-9753401Q2A	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753401Q2A SNJ54LVC08AFK	Samples
5962-9753401QCA	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753401QCA SNJ54LVC08AJ	Samples
5962-9753401QDA	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753401QDA SNJ54LVC08AW	Samples
SN74LVC08ABQAR	ACTIVE	WQFN	BQA	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC08A	Samples
SN74LVC08AD	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC08A	Samples
SN74LVC08ADBR	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC08A	Samples
SN74LVC08ADBRE4	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC08A	Samples
SN74LVC08ADE4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC08A	Samples
SN74LVC08ADG4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC08A	Samples
SN74LVC08ADR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	LVC08A	Samples
SN74LVC08ADRE4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC08A	Samples
SN74LVC08ADRG3	ACTIVE	SOIC	D	14	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	LVC08A	Samples
SN74LVC08ADRG4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC08A	Samples
SN74LVC08ADT	ACTIVE	SOIC	D	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC08A	Samples
SN74LVC08ANSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC08A	Samples
SN74LVC08ANSRE4	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC08A	Samples
SN74LVC08APW	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC08A	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC08APWG4	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC08A	Samples
SN74LVC08APWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	LC08A	Samples
SN74LVC08APWRE4	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC08A	Samples
SN74LVC08APWRG3	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	LC08A	Samples
SN74LVC08APWRG4	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC08A	Samples
SN74LVC08APWT	ACTIVE	TSSOP	PW	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC08A	Samples
SN74LVC08APWTG4	ACTIVE	TSSOP	PW	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC08A	Samples
SN74LVC08ARGYR	ACTIVE	VQFN	RGY	14	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LC08A	Samples
SN74LVC08ARGYRG4	ACTIVE	VQFN	RGY	14	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LC08A	Samples
SNJ54LVC08AFK	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753401Q2A SNJ54LVC08AFK	Samples
SNJ54LVC08AJ	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753401QCA SNJ54LVC08AJ	Samples
SNJ54LVC08AW	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753401QDA SNJ54LVC08AW	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

[3] MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

[4] There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

[5] Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

[6] Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN54LVC08A, SN74LVC08A :

- Catalog : SN74LVC08A
- Automotive : SN74LVC08A-Q1, SN74LVC08A-Q1
- Enhanced Product : SN74LVC08A-EP, SN74LVC08A-EP
- Military : SN54LVC08A

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

- Military - QML certified for Military and Defense Applications

重要なお知らせと免責事項

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